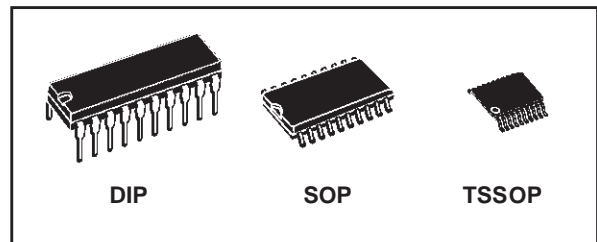




M74HCT241

OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED:
 $t_{PD} = 15 \text{ ns (TYP.)}$ at $V_{CC} = 4.5\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu\text{A(MAX.)}$ at $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS :
 $V_{IH} = 2\text{V (MIN.)}$ $V_{IL} = 0.8\text{V (MAX)}$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 6\text{mA (MIN)}$
- PIN AND FUNCTION COMPATIBLE WITH
 74 SERIES 241



ORDER CODES

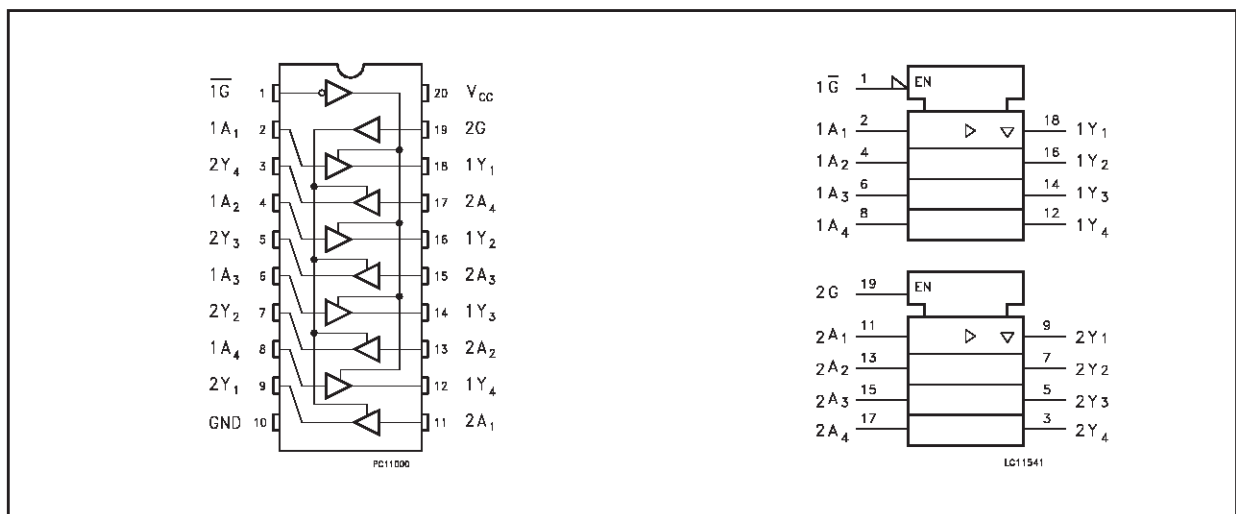
PACKAGE	TUBE	T & R
DIP	M74HCT241B1R	
SOP	M74HCT241M1R	M74HCT241RM13TR
TSSOP		M74HCT241TTR

DESCRIPTION

The 74HCT241 is an advanced high-speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with silicon gate C²MOS technology. Each control input governs four BUS BUFFERS.

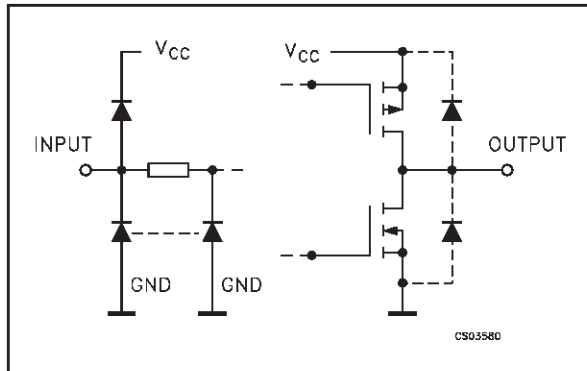
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



M74HCT241

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{1G}$	Output Enable Input
2, 4, 6, 8	1A1 to 1A4	Data Inputs
9, 7, 5, 3	2Y1 to 2Y4	Data Outputs
11, 13, 15, 17	2A1 to 2A4	Data Inputs
18, 16, 14, 12	1Y1 to 1Y4	Data Outputs
19	$\overline{2G}$	Output Enable Input
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUT	INPUTS		OUTPUT
$\overline{1G}$	1An	1Yn	$\overline{2G}$	2An	2Yn
L	L	L	H	L	L
L	H	H	H	H	H
H	X	Z	L	X	Z

X : Don't Care
Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$
T_L	Lead Temperature (10 sec)	300	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 $^{\circ}C$; derate to 300mW by 10mW/ $^{\circ}C$ from 65 $^{\circ}C$ to 85 $^{\circ}C$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	$^{\circ}C$
t_r, t_f	Input Rise and Fall Time ($V_{CC} = 4.5$ to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output Voltage	4.5	I _O = -20 μA	4.4	4.5		4.4		4.4		V
			I _O = -6.0 mA	4.18	4.31		4.13		4.10		
V _{OL}	Low Level Output Voltage	4.5	I _O = 20 μA		0.0	0.1		0.1		0.1	V
			I _O = 6.0 mA		0.17	0.26		0.33		0.40	
I _I	Input Leakage Current	5.5	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			± 0.5		± 5		± 10	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			4		40		80	μA
Δ I _{CC}	Additional Worst Case Supply Current	5.5	Per Input pin V _I = 0.5V or V _I = 2.4V Other Inputs at V _{CC} or GND			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

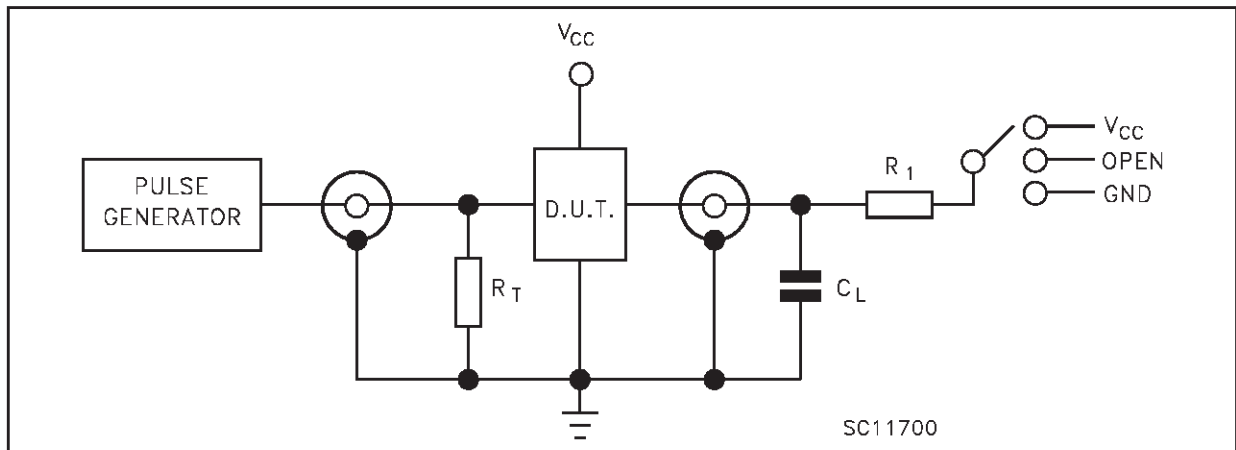
Symbol	Parameter	Test Condition		Value						Unit		
		V _{CC} (V)	C _L (pF)	T _A = 25°C			-40 to 85°C		-55 to 125°C			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
t _{TLH} t _{THL}	Output Transition Time	4.5	50		7	12		15		18	ns	
t _{PLH} t _{PHL}	Propagation Delay Time	4.5	50		15	22		28		33	ns	
		4.5	150		21	30		38		45		
t _{PLH} t _{PHL}	Propagation Delay Time	4.5	50		15	25		31		38	ns	
		4.5	150		21	33		41		50		
t _{PZL} t _{PZH}	Output Enable Time	4.5	50	R _L = 1 KΩ		17	30		38		45	ns
		4.5	150			23	38		48		57	
t _{PLZ} t _{PHZ}	Output Disable Time	4.5	50	R _L = 1 KΩ		16	30		38		45	ns

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{OUT}	Output Capacitance				10						pF
C _{PD}	Power Dissipation Capacitance (note 1)				31						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

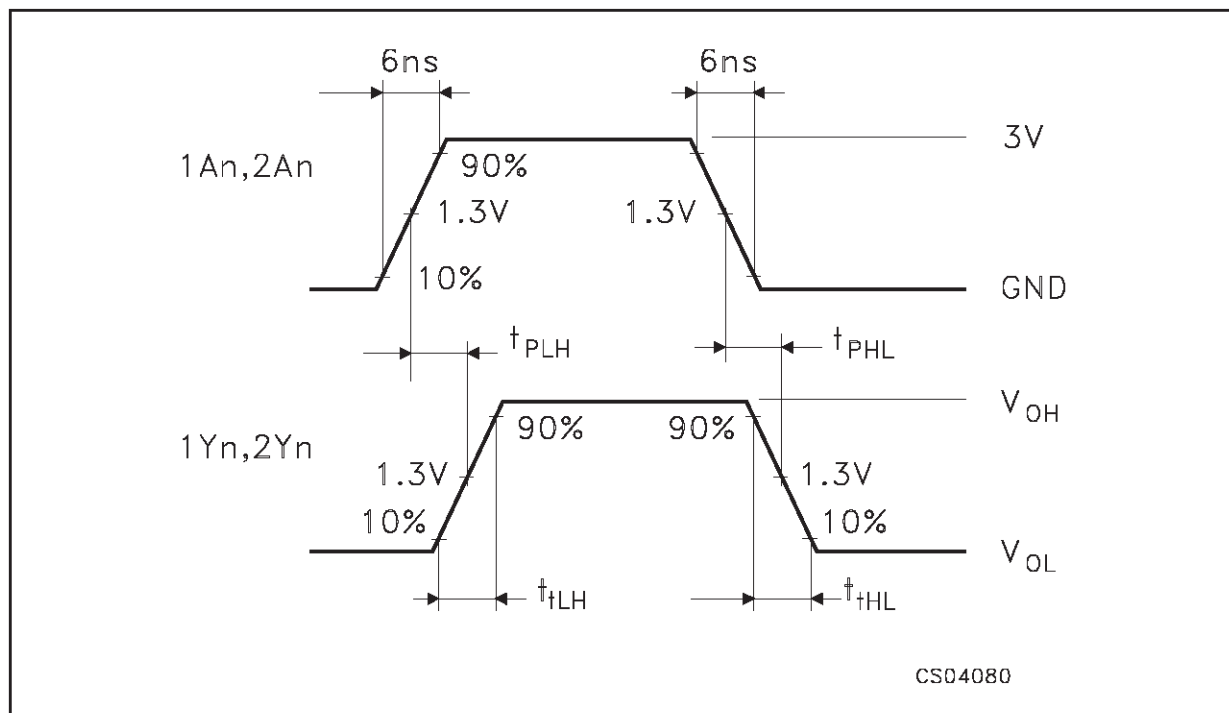
TEST CIRCUIT



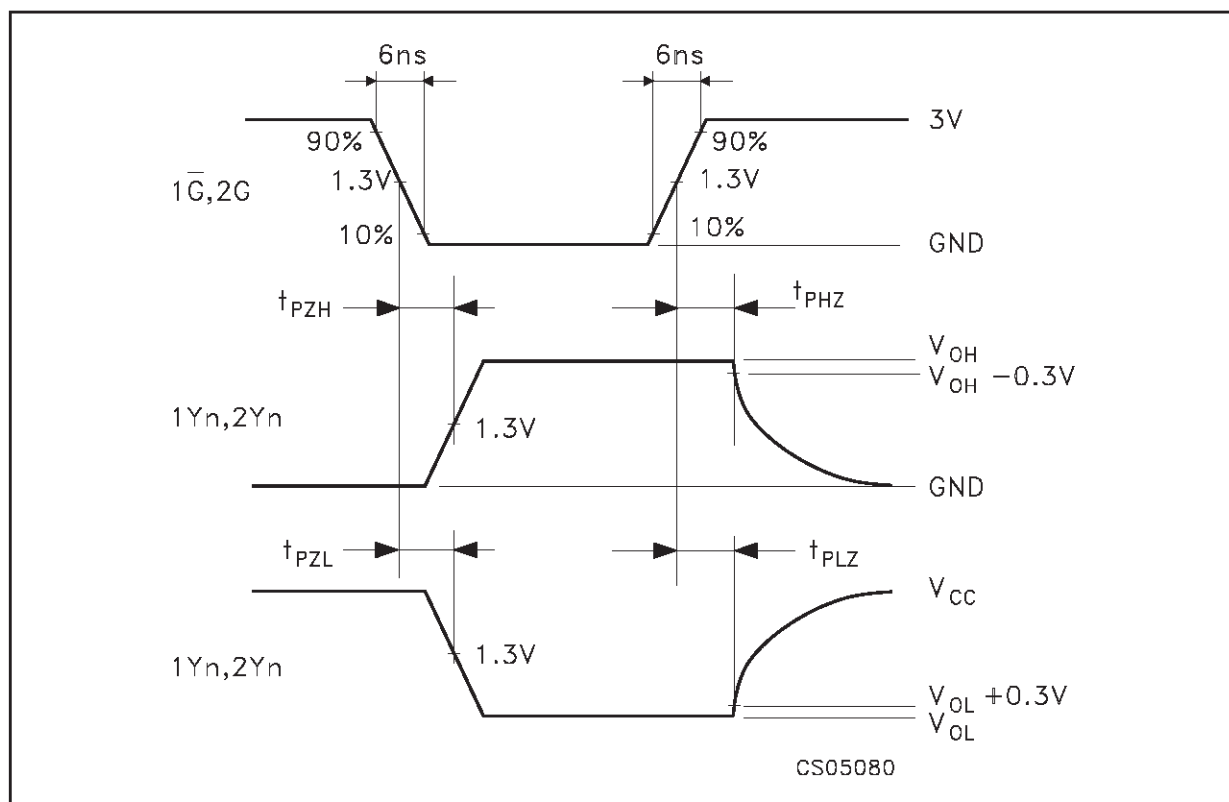
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	V _{CC}
t _{PZH} , t _{PHZ}	GND

C_L = 50pF/150pF or equivalent (includes jig and probe capacitance)
 R₁ = 1KΩ or equivalent
 R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

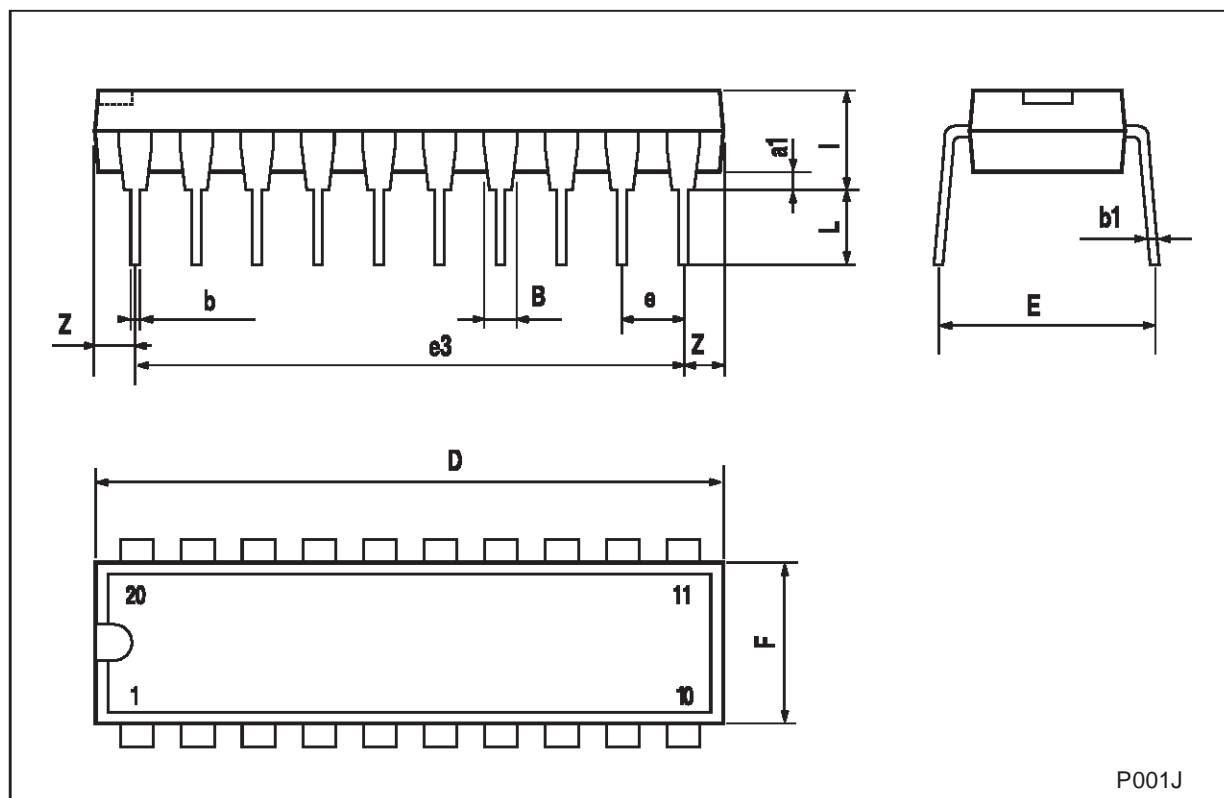


WAVEFORM 2 : OUTPUT AND ENABLE TIMES (f=1MHz; 50% duty cycle)



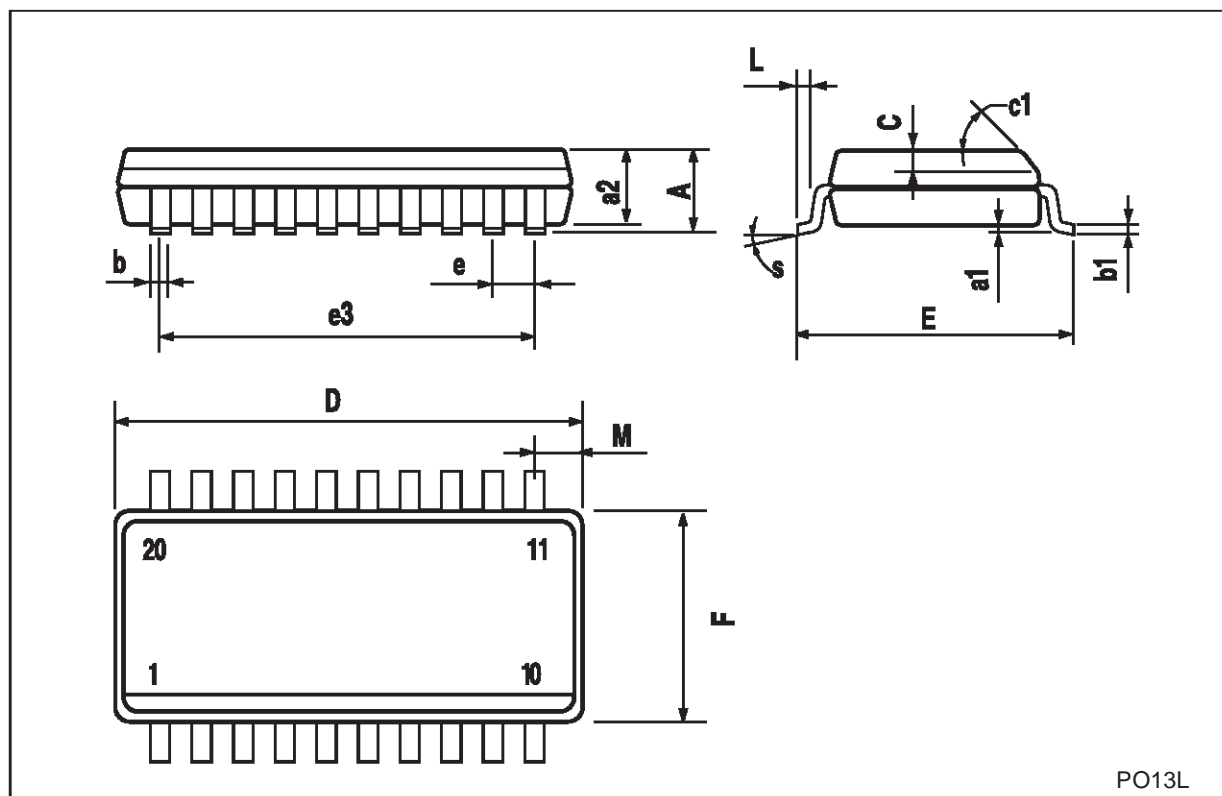
Plastic DIP-20 (0.25) MECHANICAL DATA						
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DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



SO-20 MECHANICAL DATA

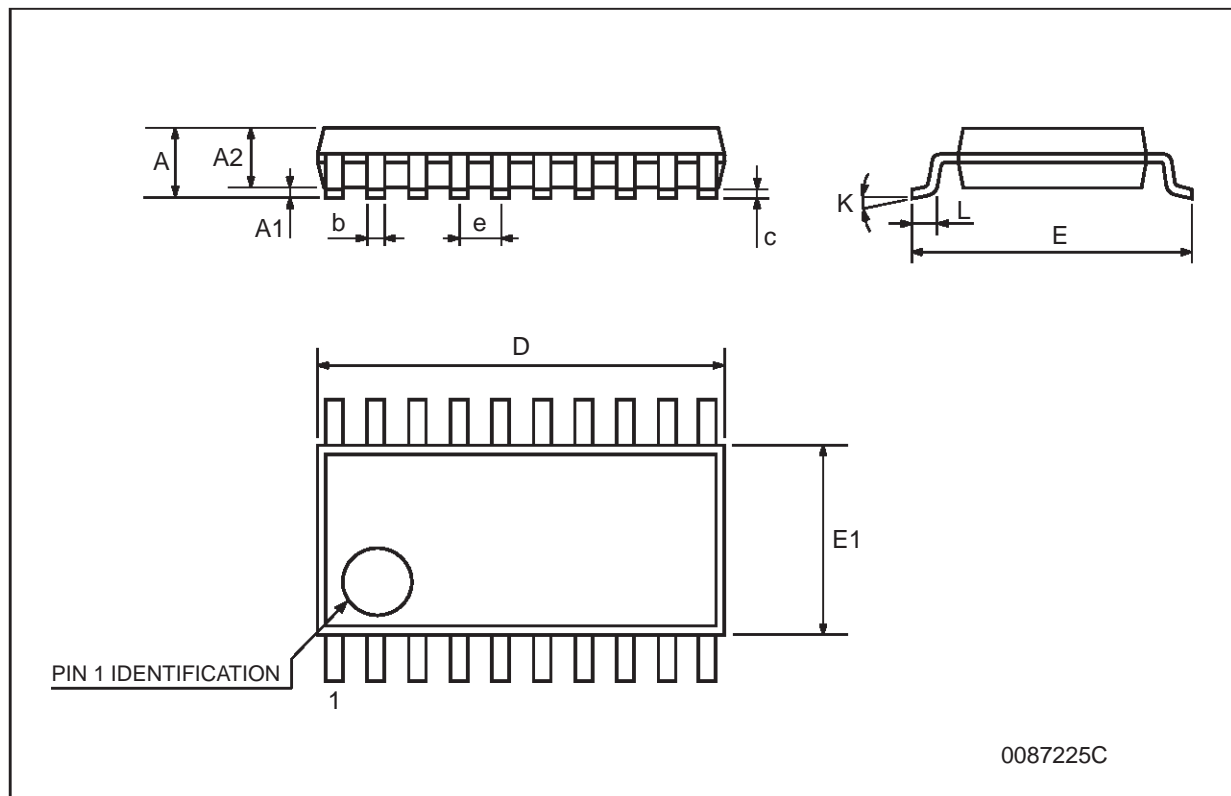
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



PO13L

TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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